

Revision 1.02

SINGLE FREQUENCY LASER DIODES Distributed Feedback Laser





General Product Information

Application
Spectroscopy
Metrology
THz Generation



Absolute Maximum Ratings

Parameter	Symbol	Unit	min	typ	max
Storage Temperature	T_S	°C	-40		85
Operational Temperature at Case	T_{C}	°C	-20		75
Operational Temperature at Laser Chip	T_LD	°C	0		50
Forward Current	I_{F}	mA			200
Reverse Voltage	V_R	V			2
Output Power	P_{opt}	mW			100
TEC Current	I_{TEC}	Α			1.8
TEC Voltage	V_{TEC}	V			3.2

Measurement Conditions / Comments

Stress in excess of one of the Absolute Maximum Ratings may damage the laser. Please note that a damaging optical power level may occur although the maximum current is not reached. These are stress ratings only, and functional operation at these or any other conditions beyond those indicated under Recommended Operational Conditions is not implied.

Recommended Operational Conditions

Parameter	Symbol	Unit	min	typ	max
Operational Temperature at Case	T_{case}	°C	-20		65
Operational Temperature at Laser Chip	T_{LD}	°C	5		40
Forward Current	I _F	mA			180
Output Power	P _{opt}	mW	20		80

Measurement Conditions / Comments
measured by integrated Thermistor

Characteristics at T_{LD} = 25° C at BOL

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	λ_{C}	nm	779	780	781
Linewidth (FWHM)	Δλ	MHz		2	
Mode-hop free Tuning Range	$\Delta \lambda_{\text{tune}}$	pm		1500	
Temperature Coefficient of Wavelength	dλ / dT	nm / K		0.06	
Current Coefficient of Wavelength	dλ / dl	nm / mA		0.003	
Sidemode Supression Ratio	SMSR	dB	30	45	
Current Coefficient of Wavelength	dλ / dl	nm / mA	30	0.003	:



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Characteristics at T _{LD}	= 25° C at BOL			cont'd	
Parameter	Symbol	Unit	min	typ	max
Mode-hop free Temperature Range	T _{LD}	° C	15		40
Mode-hop free Power Range	P _{opt}	mW	20		80
Laser Current @ P _{opt} = 80 mW	I_{LD}	mA			180
Slope Efficiency	η	W/A	0.6	0.8	1.1
Threshold Current	I _{th}	mA			70
Divergence parallel (FWHM)	$\Theta_{ }$	0		8	
Divergence perpendicular (FWHM)	Θ_{\perp}	0		21	
Degree of Polarization	DOP	%		90	

Measurement Conditions / Comments	
Temperature at Laser Chip	
parallel to short axis of the housing (see p. 3)	
parallel to long axis of the housing (see p. 3)	
80 mW; E field parallel to long axis of housing	1

Monitor Diode					
Parameter	Symbol	Unit	min	typ	max
Monitor Detector Responsivity	I _{mon} / P _{opt}	μA/mW	1		20

Meas	surement Conditions / Comments	
$J_R =$	5 V	

Thermoelectric Cooler					
Parameter	Symbol	Unit	min	typ	max
Current	I _{TEC}	А		0.4	
Voltage	U_TEC	V		0.8	
Power Dissipation (total loss at case)	P _{loss}	W		0.5	
Temperature Difference	ΔΤ	K			50

Measurement Conditions / Comments
$P_{opt} = 80 \text{ mW}, \Delta T = 20 \text{ K}$
$P_{opt} = 80 \text{ mW}, \Delta T = 20 \text{ K}$
$P_{opt} = 80 \text{ mW}, \Delta T = 20 \text{ K}$
$P_{opt} = 80 \text{ mW}, \Delta T = T case - TLD $

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Зупірої	Unit	min	цур	max
R	kΩ		10	
β			3892	
А		1.1293 x 10 ⁻³		
В		2.3410 x 10 ⁻⁴		
C			8.7755 x 10	-8
	β A	R kΩ β A	R kΩ β A B	R kΩ 10 β 3892 A 1.1293 x 10

Measurement Conditions / Comments					
$T_{LD} = 25^{\circ} C$					
$R_1 / R_2 = e^{\beta (1/T_1 \cdot 1/T_2)} $ at $T_{LD} =$	0° 50° C				
$1/T = A + B(\ln R) + C(\ln R)^3$					
T: temperature in Kelvin					
R: resistance at T in Ohm					

Thermistor (Standard NTC Type)

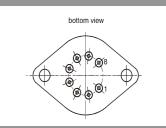


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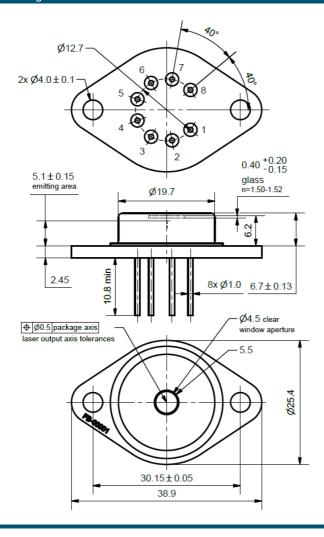
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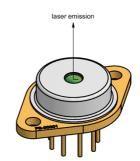


Pin Assignment							
1	Thermoelectric Cooler (+)	5	Laser Diode Anode				
2	Thermistor	6	Monitor Diode Anode				
3	Thermistor	7	Photo Diode Cathode				
4	Laser Diode Cathode	8	Thermoelectric Cooler (-)				
All	All 8 pins are isolated from case.						



Package Drawings





AIZ-16-311-1543-B



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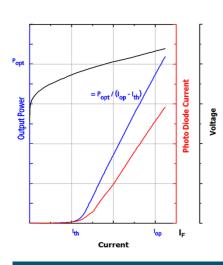
SINGLE FREQUENCY LASER DIODES **Distributed Feedback Laser**



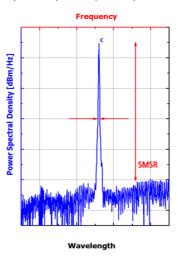


Typical Measurement Results

Output Power vs. Current



Spectra at Specified Optical Output Power



Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.

Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

The DFB laser is sensitive against optical feedback, so an optical isolator may be required in order to avoid any disturbance of the emission spectrum. Operating at moderate temperatures on proper heat sinks will contribute to a long lifetime of the diode.

Avoid direct and/or indirect exposure to the free running beam. Collimating and focussing the free running beam with optics as common in optical instruments will increase threat to the human eye.

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